

at least one thin film transistor formed over said substrate for switching said pixel electrode, said thin film transistor comprising:

a semiconductor layer having at least source, drain and channel regions and a capacitor forming portion, wherein said light shielding film is located below said semiconductor layer;

a first insulating film formed on said channel region; and

a gate electrode formed over said channel region with said first insulating film interposed therebetween,

a storage capacitor electrically connected to said thin film transistor, said storage capacitor comprising:

said capacitor forming portion of the semiconductor layer;

a capacitor forming electrode formed over said capacitor forming portion; and

a second insulating film interposed between said capacitor forming portion and said capacitor forming electrode,

wherein said second insulating film is thicker than said first insulating film.

23. (Currently Amended) A semiconductor device comprising:

a substrate;

a light shielding conductive layer formed over said substrate;

a first insulating film formed on said light shielding conductive layer;

a semiconductor layer formed on said first insulating film, said semiconductor layer having at least a pair of impurity regions and a channel region extending therebetween and a capacitor forming portion, wherein said light shielding conductive layer is located below said semiconductor layer;

a second insulating film formed on said channel region;

a third insulating film formed on said capacitor forming portion of the semiconductor layer;

a gate electrode formed over said channel region with said second insulating film interposed therebetween;

a capacitor forming electrode formed over said capacitor forming portion of the semiconductor layer with said third insulating film to form a storage capacitor, wherein said second insulating film is thicker than said third insulating film;

a fourth insulating film formed over said storage capacitor and said gate electrode;

an electrode formed on said fourth insulating film;

a fifth insulating film formed over said fourth insulating film and said electrode;

a black mask formed on said fifth insulating film;

a sixth insulating film formed over said fifth insulating film and said black mask; and

a pixel electrode formed on said sixth insulating film and electrically connected to one of said pair of impurity regions.

28. (Currently Amended) A projector comprising:

a light source; and

a liquid crystal panel for modulating light from said light source, said liquid crystal panel comprising:

a substrate;

a light shielding conductive layer formed over said substrate;

at least one pixel electrode formed over said substrate;

at least one thin film transistor formed over said substrate for switching said pixel electrode, said thin film transistor comprising:

a semiconductor layer having at least source, drain and channel regions and a capacitor forming portion, wherein said light shielding conductive layer is located below said semiconductor layer;

a first insulating film formed on said channel region; and

a gate electrode formed over said channel region with said first insulating film interposed therebetween,

a storage capacitor electrically connected to said thin film transistor, said storage capacitor comprising:

said capacitor forming portion of the semiconductor layer;

a capacitor forming electrode formed over said capacitor forming portion; and

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cut. a second insulating film interposed between said capacitor forming portion and said capacitor forming electrode,

wherein said second insulating film is thicker than said first insulating film.

29. (Currently Amended) A projector comprising:

a light source; and

a liquid crystal panel for modulating light from said light source, said liquid crystal panel comprising:

a substrate;

a light shielding conductive layer formed over said substrate;

a first insulating film formed on said light shielding conductive layer;

a semiconductor layer formed on said first insulating film, said semiconductor layer having at least a pair of impurity regions and a channel region extending therebetween and a capacitor forming portion, wherein said light shielding conductive layer is located below said semiconductor layer;

a second insulating film formed on said channel region;

a third insulating film formed on said capacitor forming portion of the semiconductor layer;

a gate electrode formed over said channel region with said second insulating film interposed therebetween;

a capacitor forming electrode formed over said capacitor forming portion of the semiconductor layer with said third insulating film to form a storage capacitor, wherein said second insulating film is thicker than said third insulating film;

a fourth insulating film formed over said storage capacitor and said gate electrode;

an electrode formed on said fourth insulating film;

a fifth insulating film formed over said fourth insulating film and said electrode;

a black mask formed on said fifth insulating film;

a sixth insulating film formed over said fifth insulating film and said black mask; and

a pixel electrode formed on said sixth insulating film and electrically connected to one of said pair of impurity regions.

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